

MOSFETs Silicon N-Channel MOS (U-MOSVI-H)

# TPC8228-H

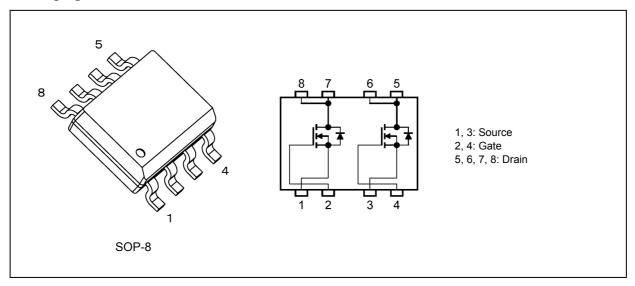
#### 1. Applications

- · DC-DC Converters
- · CCFL Inverters

#### 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 2.6 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 38 \text{ m}\Omega$  (typ.)
- (5) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (6) Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.1 \text{ mA})$

#### 3. Packaging and Internal Circuit





### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	60	V
Gate-source voltage			$V_{GSS}$	±20	
Drain current (DC)		(Note 1)	$I_D$	3.8	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	15.2	
Power dissipation (single operation)	(t = 10 s)	(Note 2), (Note 4)	P <sub>D(1)</sub>	1.5	W
Power dissipation (per device for dual operation)	(t = 10 s)	(Note 2), (Note 5)	P <sub>D(2)</sub>	1.1	
Power dissipation (single operation)	(t = 10 s)	(Note 3), (Note 4)	P <sub>D(1)</sub>	0.75	
Power dissipation (per device for dual operation)	(t = 10 s)	(Note 3), (Note 5)	P <sub>D(2)</sub>	0.45	
Single-pulse avalanche energy		(Note 6)	E <sub>AS</sub>	10	mJ
Avalanche current			I <sub>AR</sub>	3.8	Α
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

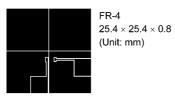
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics				Max	Unit
Channel-to-ambient thermal resistance (single operation)	(t = 10 s)	(Note 2), (Note 4)	R <sub>th(ch-a)(1)</sub>	83.3	°C/W
Channel-to-ambient thermal resistance (per device for dual operation)	(t = 10 s)	(Note 2), (Note 5)	R <sub>th(ch-a)(2)</sub>	113	
Channel-to-ambient thermal resistance (single operation)	(t = 10 s)	(Note 3), (Note 4)	R <sub>th(ch-a)(1)</sub>	166	
Channel-to-ambient thermal resistance (per device for dual operation)	(t = 10 s)	(Note 3), (Note 5)	R <sub>th(ch-a)(2)</sub>	277	

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4: Power dissipation and thermal resistance values per device with the other device being off (During single operation, power is supplied to only one of the two devices.)
- Note 5: Power dissipation and thermal resistance values per device for dual operation (During dual operation, power is evenly supplied to both devices.)
- Note 6:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25°C (initial), L = 1.0 mH,  $I_{AR}$  = 3.8 A





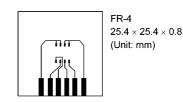


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20  \text{V} ,  V_{DS} = 0  \text{V}$	_	_	±0.1	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60			٧
Drain-source breakdown voltage (Note 7)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	43	_		
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.1 mA	1.3	_	2.3	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1.9 A	_	43	64	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.9 A	_	38	57	

Note 7: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	640	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	25	_	
Output capacitance	C <sub>oss</sub>		_	90	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz	_	3.2	4.6	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	1.8	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	6.7	_	
Switching time (fall time)	t <sub>f</sub>		_	1.8	_	
Switching time (turn-off time)	t <sub>off</sub>		_	18		

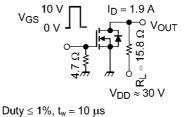


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}$ C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.8 \text{ A}$	_	11		nC
gate-drain)		$V_{DD} \approx 48 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 3.8 \text{ A}$	_	5.7		
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3.8 \text{ A}$		2.1		
Gate-drain charge	$Q_{gd}$			1.8		
Gate switch charge	$Q_{SW}$		_	2.6		

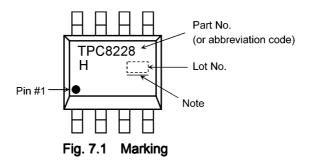
## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 8)	$I_{DRP}$	_	_	_	15.2	Α
Diode forward voltage		$V_{DSF}$	I <sub>DR</sub> = 3.8 A, V <sub>GS</sub> = 0 V	_		-1.2	V

Note 8: Ensure that the channel temperature does not exceed 150°C.



## 7. Marking (Note)



Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)

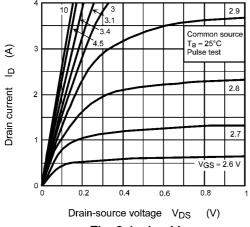


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

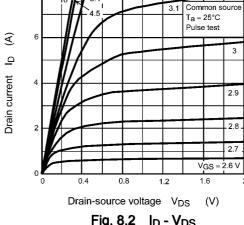


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

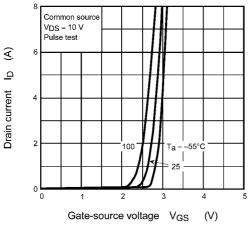


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

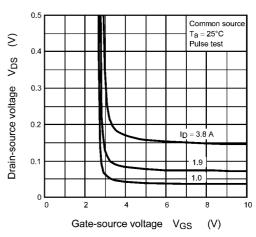


Fig. 8.4 VDS - VGS

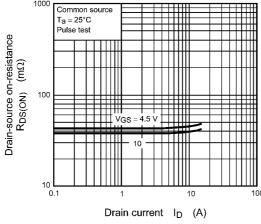


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

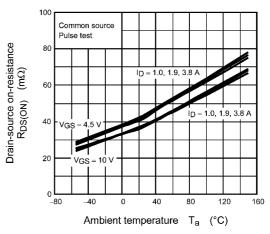


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>

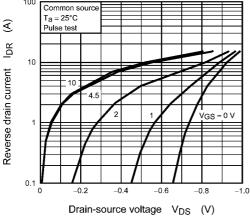


Fig. 8.7 IDR - VDS

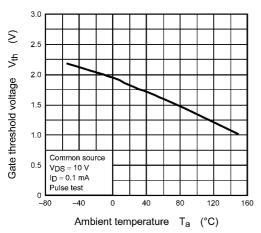


Fig. 8.9 Vth - Ta

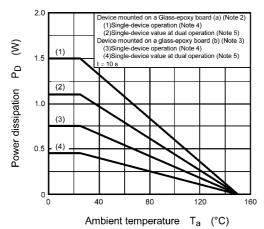


Fig. 8.11 P<sub>D</sub> - T<sub>a</sub> (Guaranteed Maximum)

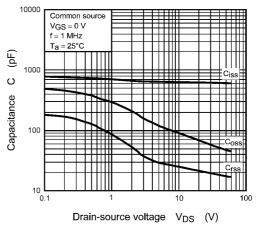


Fig. 8.8 Capacitance - V<sub>DS</sub>

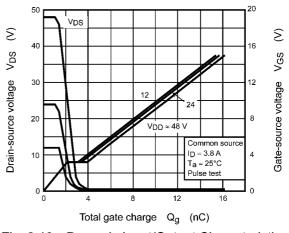


Fig. 8.10 Dynamic Input/Output Characteristics

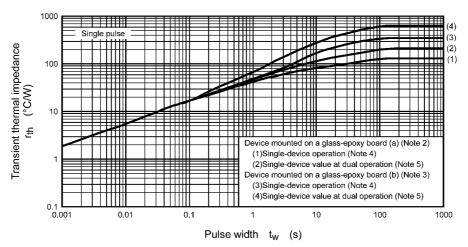


Fig. 8.12 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

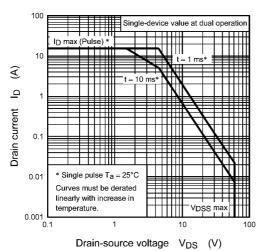


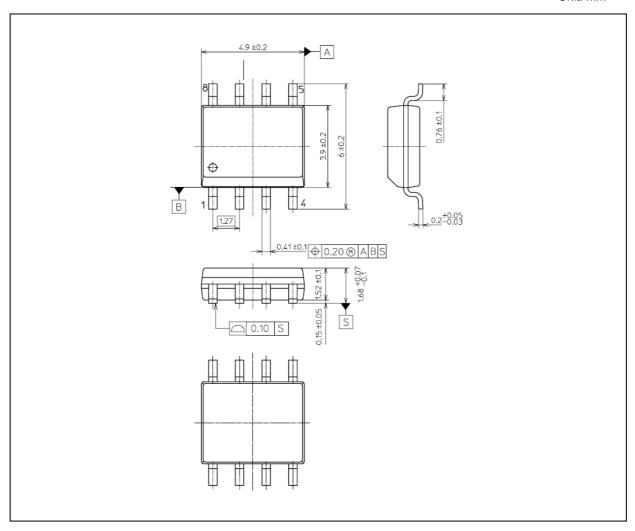
Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 0.085 g (typ.)

	Package Name(s)
TOSHIBA: 2-5R1S	
Nickname: SOP-8	

Rev.1.0



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